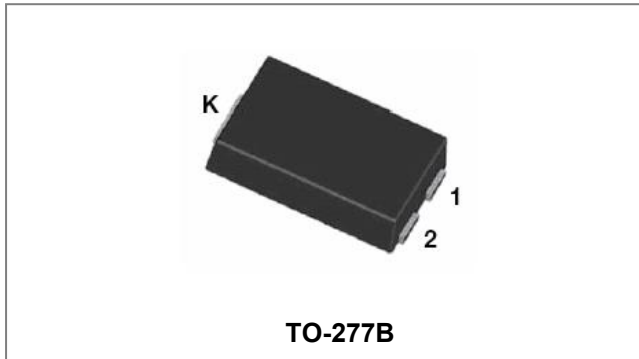


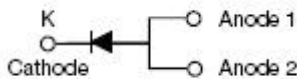
ST5150S SCHOTTKY RECTIFIER



Features

- 150°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	150	V
Average Rectified Forward Current	I _{F(AV)}	50% duty cycle @T _C =105°C, rectangular wave form	5	A
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3ms, Half Sine pulse, T _c = 25 °C	80	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 2A, Pulse, T _J = 25 °C	0.68	0.70	V
		@ 5A, Pulse, T _J = 25 °C	1.09	1.20	
Reverse Current*	I _{R1}	@V _R = rated V _R , T _J = 25 °C	0.001	0.1	mA
		@V _R = rated V _R , T _J = 125 °C	3	15	
Junction Capacitance	C _T	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	200	-	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

* Pulse width < 300 μs, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-	-55 to +150	$^{\circ}\text{C}$
Typical Thermal Resistance Junction to Ambient (NOTE1)	$R_{\theta JA}$	DC operation	75	$^{\circ}\text{C/W}$
Typical Thermal Resistance Junction to Lead (NOTE1)	$R_{\theta JL}$	DC operation	4	$^{\circ}\text{C/W}$
Approximate Weight	wt	-	0.08	g

NOTE: 1. Units mounted on P.C.B., 0.5 x 0.5" (30 x 30mm) copper pads.

Ratings and Characteristics Curves

Figure 1
Typical Forward Characteristics

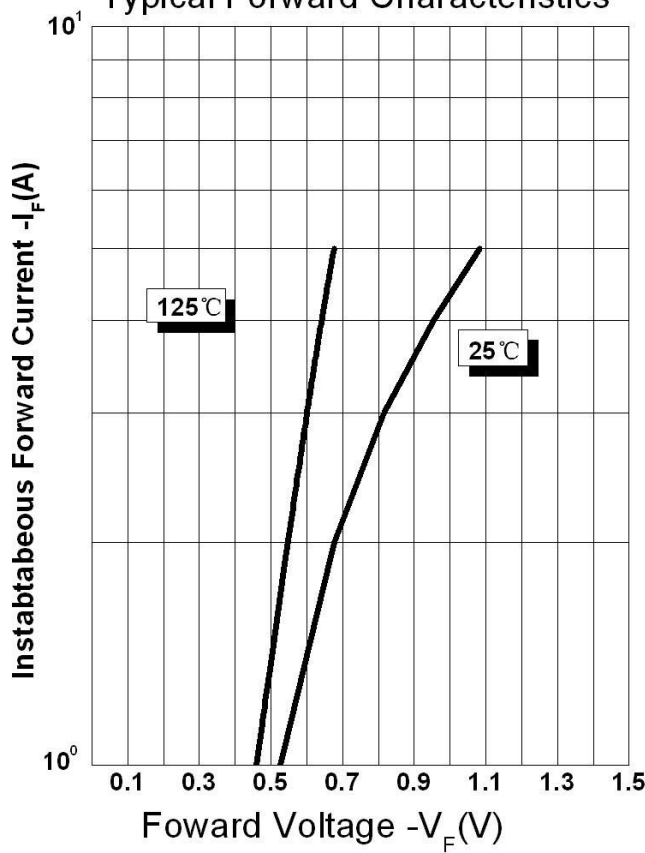


Figure 2
Typical Reverse Characteristics

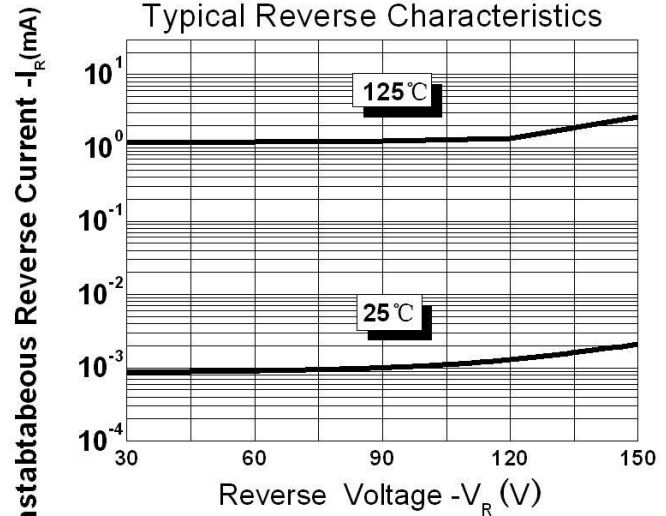
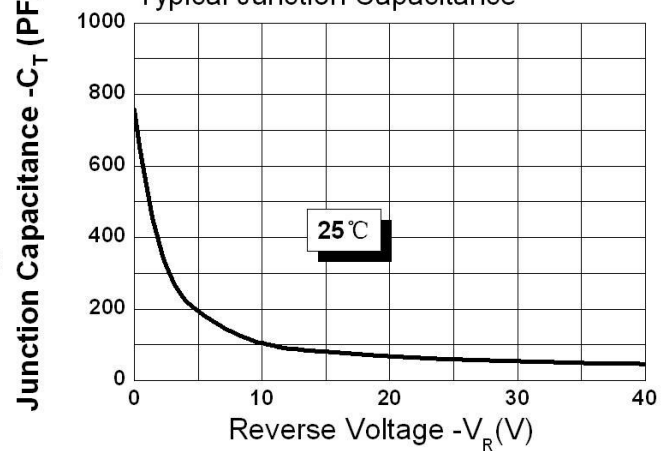
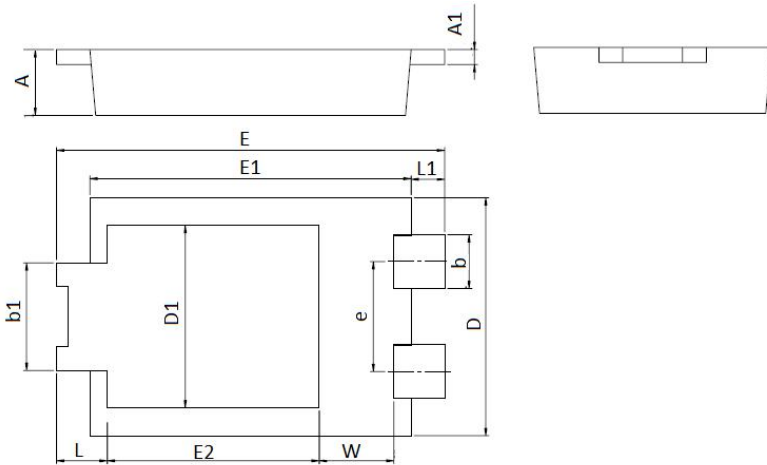
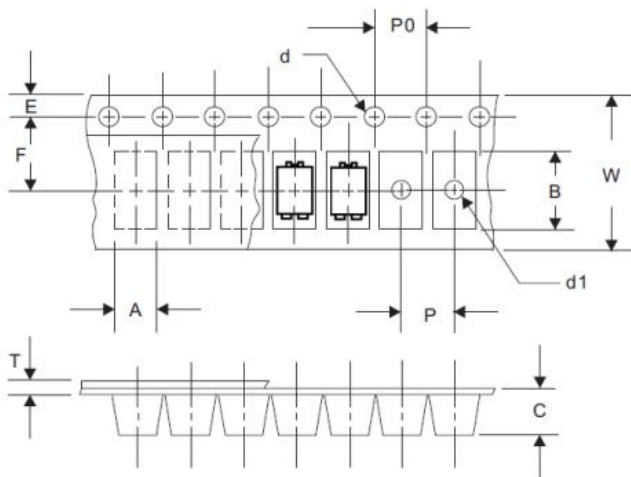


Figure 3
Typical Junction Capacitance



Mechanical Dimensions TO-277B


SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.95	1.25	0.037	0.049
A1	0.20	0.30	0.008	0.012
b	0.85	0.95	0.033	0.037
b1	1.70	1.90	0.067	0.075
D	3.88	4.08	0.153	0.161
D1	2.90	3.20	0.114	0.126
e	1.74	1.94	0.069	0.076
E	6.30	6.70	0.248	0.264
E1	5.28	5.48	0.208	0.216
E2	3.40	3.70	0.134	0.146
L	0.70	1.00	0.028	0.039
L1	0.41	0.71	0.016	0.028
W	1.10	1.40	0.043	0.055

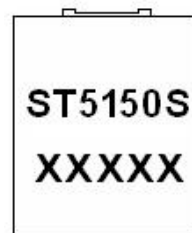
Carrier Tape Specification TO-277B


SYMBOL	Millimeters	
	Min.	Max.
A	4.28	4.48
B	6.80	7.10
C	1.30	1.50
d	1.40	1.60
d1	-	1.50
E	1.65	1.85
F	5.40	5.60
P	7.90	8.10
P0	3.90	4.10
T	0.24	0.44
W	11.70	12.30

Ordering Information

Device	Package	Shipping
ST5150S	TO-277B(Pb-Free)	5000pcs/ reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram


Mark Spec

Where XXXXX is YYWWL

ST = Device Type
 5 = Forward Current (5A)
 150 = Reverse Voltage (150V)
 S = Package type
 YY = Year
 WW = Week
 L = Lot Number

Cautions: Molding resin
 Epoxy resin UL:94V-0

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